

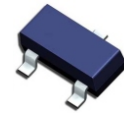
SMD Switching Diode



SMD Diodes Specialist

CDST226-G

RoHS Device



Features

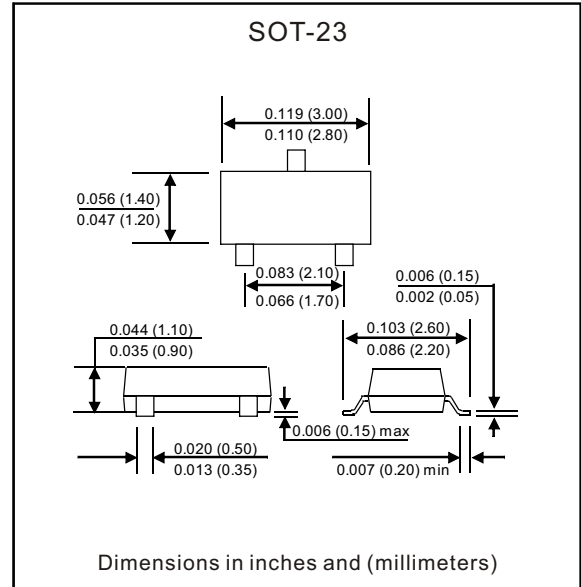
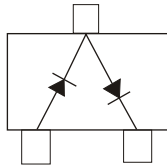
-Power dissipation: 150mW (@ $T_A=25^{\circ}\text{C}$)

Mechanical data

Case: SOT-23

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

Marking: C3



Maximum Rating (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive peak reverse voltage	V_{RM}	85	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	80	V
Forward continuous current	I_{FM}	300	mA
Average rectified output current	I_o	100	mA
Peak forward surge current @1 μS @1.0S	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Storage temperature range	T_{STG}	-55 ~ +125	$^{\circ}\text{C}$

Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V_{BR}	$I_R=100\mu\text{A}$	80		V
Reverse leakage current	I_R	$V_R=80\text{V}$		0.5	μA
Forward voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode capacitance	C_T	$V_R=0\text{V}$, $f=1\text{MHz}$		3	pF
Reverse recovery time	t_{rr}			4	nS

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Electrical and Characteristic Curves (CDST226-G)

Fig. 1 - Forward Characteristics

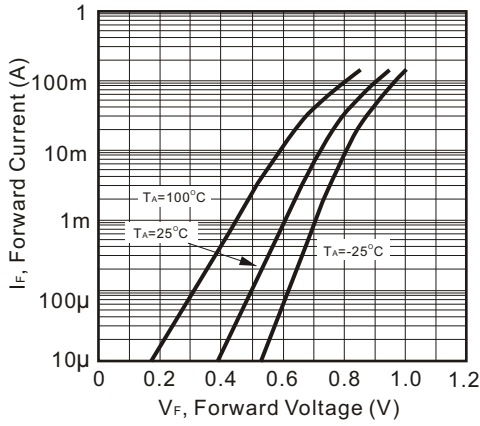


Fig. 2 - Reverse Characteristics

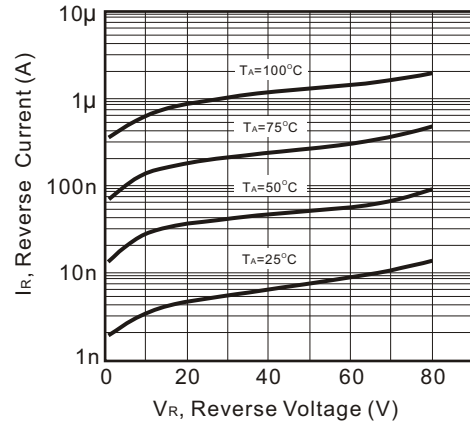


Fig. 3 - Diode Capacitance

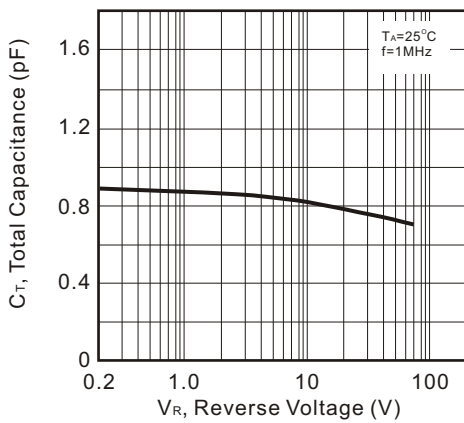


Fig. 4 - Reverse Recovery Characteristics

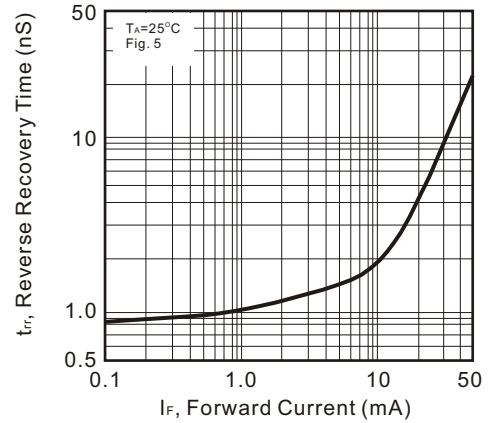


Fig. 5 - Reverse Recovery Time (t_{rr}) Test Circuit

